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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China













SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

| V _{DS} (V) | $R_{DS(on)}(\Omega)(max)$ | I _D (A) |
|---------------------|----------------------------|--------------------|
| 600 | 700 @ V _{GS} = 0V | 0.03 |

Features

- **Depletion Mode**
- Low Gate Charge

Application

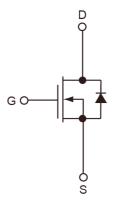
- Converters
- Telecom

Ordering Information

| Part No. | Package | Packing | | |
|--------------|---------|-----------------|--|--|
| TSM126CX RFG | SOT-23 | 3kpcs / 7" Reel | | |

Note: "G" denotes Halogen Free Product.

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|--|---------|-----------------------------------|-------------|------|
| Drain-Source Voltage | | V _{DS} | 600 | V |
| Gate-Source Voltage | | V_{GS} | ±20 | V |
| Continuous Drain Current | Tc=25°C | | 0.030 | Α |
| Continuous Drain Current | Tc=70°C | l _D | 0.024 | А |
| Pulsed Drain Current ^a | | I _{DM} | 0.120 | А |
| Maximum Power Dissipation | | P _D | 0.5 | W |
| Soldering Temperature ^b | | TL | 300 | °C |
| Operating Junction Temperature | | TJ | +150 | °C |
| Operating Junction and Storage Temperature F | Range | T _J , T _{STG} | -55 to +150 | °C |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|---|----------------|-------|------|
| Thermal Resistance, Junction to Ambient | $R\Theta_{JA}$ | 250 | °C/W |

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Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Distance of 1.6mm from case for 10 seconds.

Version: A14



N-Channel Depletion-Mode MOSFET



Electrical Specifications (Tj = 25°C unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Тур | Max | Unit |
|----------------------------------|--|----------------------|-------|-------|-------|------|
| Static ^a | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = -5V, I_D = 250\mu A$ | BV _{DSS} | 600 | | | V |
| Gate Threshold Voltage | $V_{DS} = 3V, I_{D} = 8\mu A$ | $V_{GS(TH)}$ | -2.7 | -1.8 | -1.0 | V |
| Drain-Source cutoff current | $V_{DS} = 600V, V_{GS} = -5V,$ $Ta = 25^{\circ}C$ | | | | 0.1 | μA |
| Drain-Source cutoff current | $V_{DS} = 480V, V_{GS} = -5V,$ Ta = 125°C | I _{DS(OFF)} | | | 10 | μA |
| Gate-Source Leakage Current | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I _{GSS} | | | ±10 | μA |
| On-state Drain Current | $V_{DS} = 25V, V_{GS} = 0V$ | I _{DSS} | 12 | | | mA |
| | $V_{GS} = 0V$, $I_D = 3mA$ | | | 350 | 700 | Ω |
| Drain-Source On-State Resistance | V _{GS} = 10V, I _D = 16mA | $R_{DS(ON)}$ | | 400 | 800 | Ω |
| Forward Transconductance | $ V_{DS} > 2 I_{D} R_{DS(ON)max},$ $I_{D} = 0.01A$ | g _{fs} | 0.008 | 0.017 | | S |
| Dynamic | | | | • | | |
| Input Capacitance |)/ O5)/)/ 5)/ | C _{iss} | | 51.42 | | pF |
| Output Capacitance | $V_{DS} = 25V, V_{GS} = -5V,$ | C _{oss} | | 4.48 | | |
| Reverse Transfer Capacitance | f = 1.0MHz | C_{rss} | | 1.12 | | |
| Total Gate Charge | \/ - 400\/ I - 0.04A | Q_g | | 1.18 | | |
| Gate-Source Charge | $V_{DS} = 400V, I_D = 0.01A,$ $V_{GS} = -5V \text{ to } 5V$ | Q_gs | | 0.49 | | nC |
| Gate-Drain Charge | V _{GS} = -5V 10 5V | Q_{gd} | | 0.365 | | |
| Switching | | | | | | |
| Turn-On Delay Time | ., | t _{d(on)} | | 10.01 | | |
| Turn-On Rise Time | $V_{DD} = 300V, I_D = 0.01A,$ | t _r | | 55.7 | | ns |
| Turn-Off Delay Time | V_{GS} = -5V to 7V, R_{G} = 6Ω | $t_{d(off)}$ | | 57.2 | | |
| Turn-Off Fall Time | | t _f | | 135.5 | | |
| Source-Drain Diode | | | | | | |
| Diode forward Current | Continuous | I _S | | | 0.025 | Α |
| Diode Pulse Current | | I _{SM} | | | 0.100 | Α |
| Diode Forward Voltage | I _{SD} = 16mA, V _{GS} = -5V | V_{SD} | | | 1.2 | V |
| Reverse Recovery Time | I _F =0.01A, V _{GS} =-10V | trr | | 243.1 | | ns |
| Reverse Recovery Charge | dl _F /dt=100A/µs, V _R =30V | Qrr | | 639 | | nC |

Notes:

a. pulse test: PW $\leqslant\!380\mu s,$ duty cycle $\leqslant\!2\%$

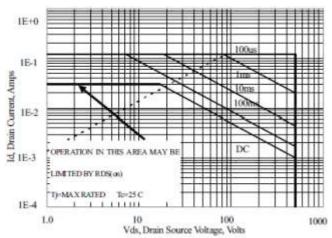


N-Channel Depletion-Mode MOSFET

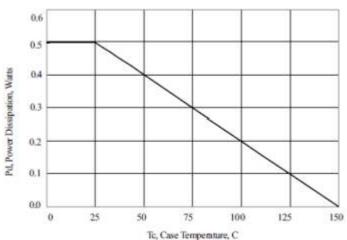


Electrical Characteristics Curves (Ta = 25°C, unless otherwise noted)

Maximum Forward Bias Safe Operation Area

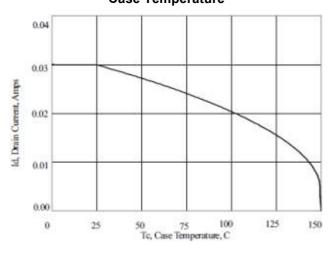


Maximum Power Dissipation vs. Case Temperature

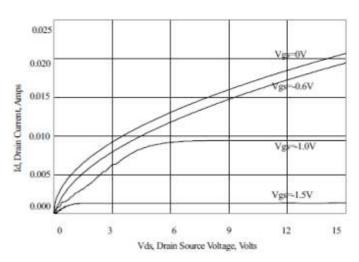


Maximum Continuous Drain Current vs.

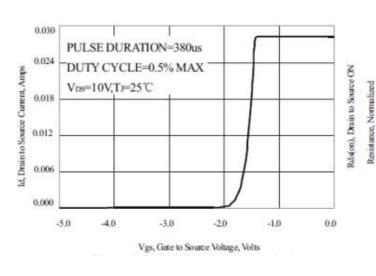
Case Temperature



Typical Output Characteristics

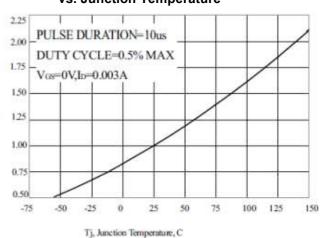


Typical Transfer Characteristics



Drain to Source ON Resistance

vs. Junction Temperature



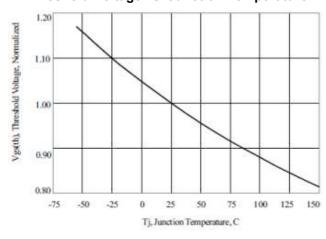




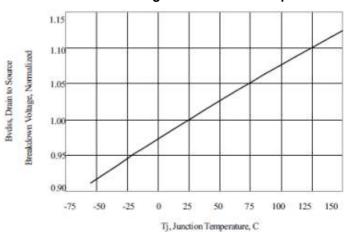
N-Channel Depletion-Mode MOSFET

Electrical Characteristics Curves (Ta = 25°C, unless otherwise noted)

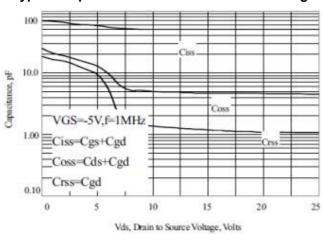
Threshold Voltage vs. Junction Temperature



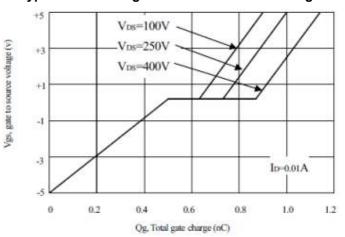
Breakdown Voltage vs. Junction Temperature



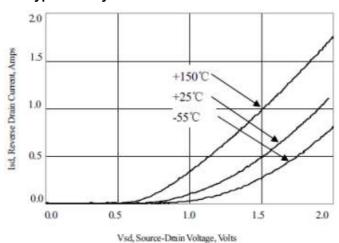
Typical Capacitance vs. Drain to source Voltage



Typical Gate Charge vs. Gate to Source Voltage



Typical Body Diode Transfer Characteristics



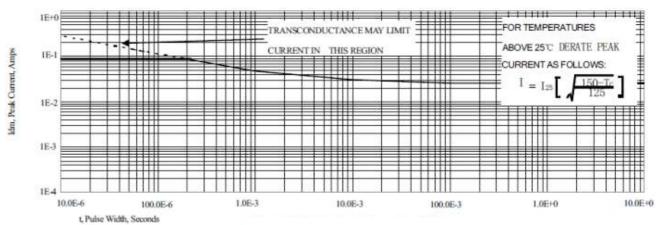


N-Channel Depletion-Mode MOSFET



Electrical Characteristics Curves (Ta = 25°C, unless otherwise noted)

Maximum Peak Current Capability

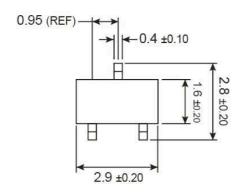


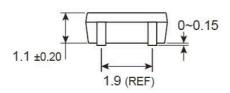


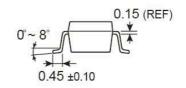
Pb RoHS

N-Channel Depletion-Mode MOSFET

SOT-23 Mechanical Drawing







Unit: Millimeters



TSM126 N-Channel Depletion-Mode MOSFET

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